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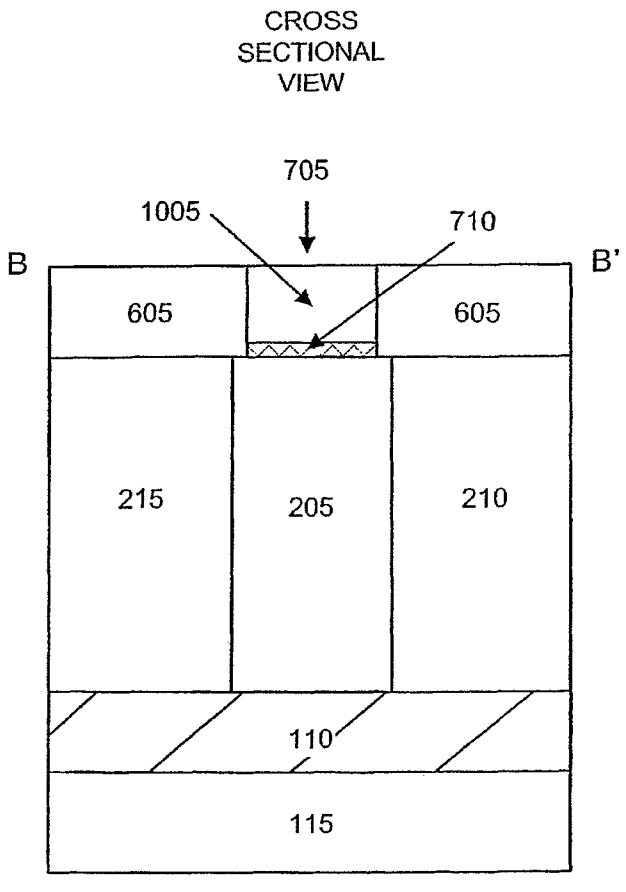
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(54) Title: NARROW-BODY DAMASCENE TRI-GATE FINFET HAVING THINNED BODY



(57) Abstract: A method of forming a fin field effect transistor includes forming a fin (205) and forming a source region (210) on a first end of the fin (205) and a drain region (215) on a second end of the fin (205). The method further includes forming a dummy gate (505) with a first semiconducting material in a first pattern over the fin (205) and forming a dielectric layer (605) around the dummy gate (505). The method also includes removing the first semiconducting material to leave a trench (705) in the dielectric layer (605) corresponding to the first pattern, thinning a portion of the fin (205) exposed within the trench (705), and forming a metal gate (1005) within the trench (705).

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